



N-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|----------------------------------|--------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}\left(\Omega\right)$ | I _D (A) | | |
| 30 | 0.050 at V _{GS} = 10 V | 3.4 | | |
| | 0.085 at V _{GS} = 4.5 V | 2.6 | | |

FEATURES

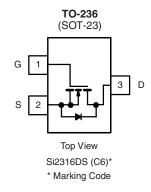
- Halogen-free Option Available
- TrenchFET® Power MOSFET



RoHS COMPLIANT

APPLICATIONS

· Battery Switch



Ordering Information: Si2316DS-T1

Si2316DS-T1-E3 (Lead (Pb)-free)

Si2316DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted | | | | | | |
|---|------------------------|-----------------------------------|--------------|------|----|--|
| Parameter | Symbol | 5 s | Steady State | Unit | | |
| Drain-Source Voltage | | V _{DS} | 30 | | V | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | V | |
| Continuous Dunin Courset /T 450 9608 h | T _A = 25 °C | - I _D | 3.4 | 2.9 | | |
| Continuous Drain Current (T _J = 150 °C) ^{a, b} | T _A = 70 °C | | 2.7 | 2.3 | | |
| Pulsed Drain Current ^b | | I _{DM} | 16 | | Α | |
| Continuous Source Current (Diode Conduction) ^{a, b} | | I _S | 0.8 | | | |
| D | T _A = 25 °C | P _D | 0.96 | 0.7 | W | |
| Power Dissipation ^{a, b} | T _A = 70 °C |] ' ['] D | 0.6 | 0.45 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Manipulation to Australia | t ≤ 5 s | R _{thJA} | 100 | 130 | | |
| Maximum Junction-to-Ambient ^a | Steady State | ¹ ¹thJA | 140 | 175 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 60 | 75 | | |

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.
- * Pb containing terminations are not RoHS compliant, exemptions may apply.

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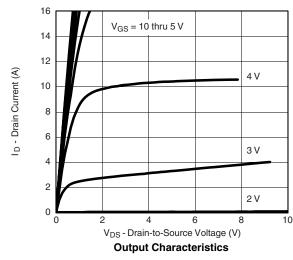
| SPECIFICATIONS T _A = 25 °C, unless otherwise noted | | | | | | | |
|--|---------------------|--|--------|-------|-------|------|--|
| | | | Limits | | | | |
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 30 | | | V | |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 0.8 | | | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | | ± 100 | nA | |
| Zara Cata Valtaga Drain Current | | V _{DS} = 30 V, V _{GS} = 0 V | | | 0.5 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | 10 | μΑ | |
| | 1 | $V_{DS} \ge 4.5 \text{ V}, V_{GS} = 10 \text{ V}$ | 6 | | | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 4.5 \text{ V}, V_{GS} = 4.5 \text{ V}$ | 4 | | | A | |
| | Б | $V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$ | | 0.042 | 0.050 | | |
| Drain-Source On-Resistance ^a | R _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 2.6 \text{ A}$ | | 0.068 | 0.085 | Ω | |
| Forward Transconductance ^a | 9 _{fs} | $V_{DS} = 4.5 \text{ V}, I_D = 3.4 \text{ A}$ | | 6.0 | | S | |
| Diode Forward Voltage | V_{SD} | I _S = 0.8 A, V _{GS} = 0 V | | 0.8 | 1.2 | V | |
| Dynamic ^b | • | | • | • | • | | |
| Total Gate Charge | Q_g | | | 4.3 | 7 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$ | | 0.65 | | nC | |
| Gate-Drain Charge | Q_{gd} | | | 1.2 | | 1 | |
| Input Capacitance | C _{iss} | | | 215 | | | |
| Output Capacitance | C _{oss} | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | | 90 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 55 | | 1 | |
| Switching | • | | | | • | | |
| Turn-On Delay Time | t _{d(on)} | | | 9 | 15 | | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 15 Ω | | 9 | 15 | ns | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong$ 1.0 A, V_{GEN} = 10 V, R_G = 6 Ω | | 14 | 20 | | |
| Fall Time | t _f | | | 6 | 12 | | |

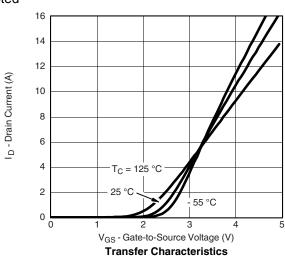
Notes:

- a. Pulse test; PW $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



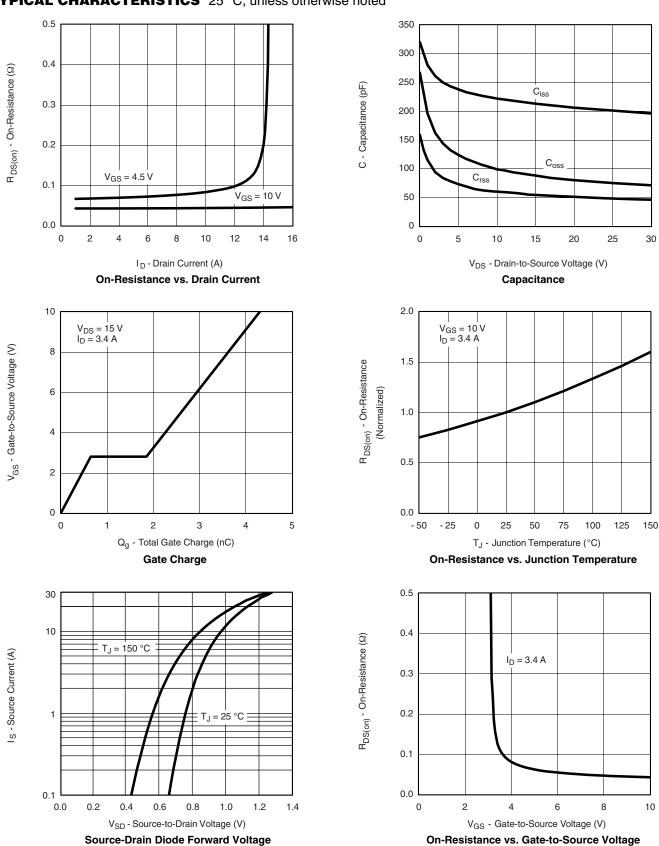








TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

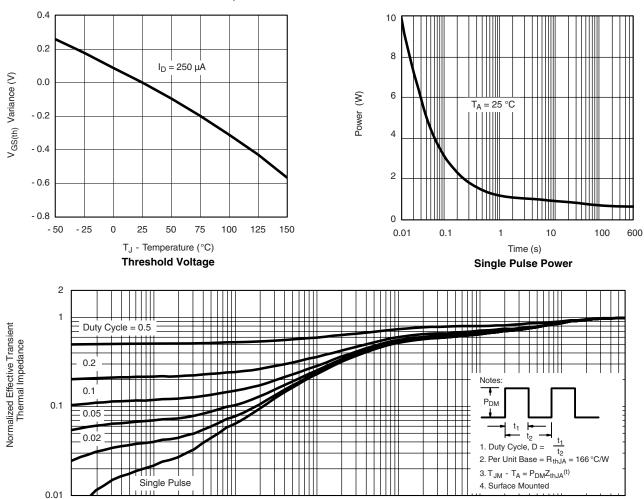


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient

10-1

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10-4

10-3

10-2

100

600

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SOT-23 (TO-236): 3-LEAD







| Dim | MILLI | METERS | INCHES | | |
|------------------------|----------|--------|------------|-------|--|
| | Min | Max | Min | Max | |
| Α | 0.89 | 1.12 | 0.035 | 0.044 | |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 | |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 | |
| b | 0.35 | 0.50 | 0.014 | 0.020 | |
| С | 0.085 | 0.18 | 0.003 | 0.007 | |
| D | 2.80 | 3.04 | 0.110 | 0.120 | |
| E | 2.10 | 2.64 | 0.083 | 0.104 | |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 | |
| е | 0.95 BSC | | 0.0374 Ref | | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | | |
| L | 0.40 | 0.60 | 0.016 | 0.024 | |
| L ₁ | 0.64 Ref | | 0.025 Ref | | |
| S | 0.50 Ref | | 0.020 Ref | | |
| q | 3° | 8° | 3° | 8° | |
| FCN: S-03946-Rev K 09- | lul-01 | • | | | |

ECN: S-03946-Rev. K, 09-Jul-01

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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